

2N2270

NPN SILICON TRANSISTOR



TO-39 CASE



www.centrasemi.com

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N2270 is a NPN silicon transistor, mounted in a hermetically sealed package, designed for general purpose amplifier applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** (T<sub>A</sub>=25°C unless otherwise noted)

|  | SYMBOL                            |             | UNITS |
|--|-----------------------------------|-------------|-------|
| Collector-Base Voltage                     | V <sub>CBO</sub>                  | 60          | V     |
| Collector-Emitter Voltage                  | V <sub>CER</sub>                  | 60          | V     |
| Collector-Emitter Voltage                  | V <sub>CEO</sub>                  | 45          | V     |
| Emitter-Base Voltage                       | V <sub>EBO</sub>                  | 7.0         | V     |
| Continuous Collector Current               | I <sub>C</sub>                    | 1.0         | A     |
| Power Dissipation                          | P <sub>D</sub>                    | 1.0         | W     |
| Power Dissipation (T <sub>C</sub> =25°C)   | P <sub>D</sub>                    | 5.0         | W     |
| Operating and Storage Junction Temperature | T <sub>J</sub> , T <sub>stg</sub> | -65 to +200 | °C    |
| Thermal Resistance                         | θ <sub>JA</sub>                   | 175         | °C/W  |
| Thermal Resistance                         | θ <sub>JC</sub>                   | 35          | °C/W  |

**ELECTRICAL CHARACTERISTICS:** (T<sub>C</sub>=25°C unless otherwise noted)

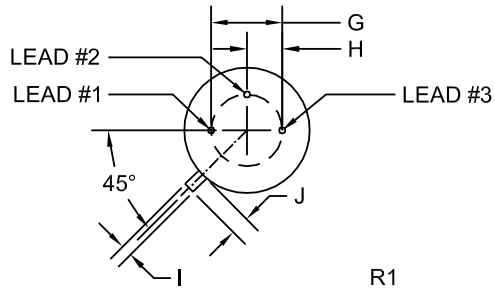
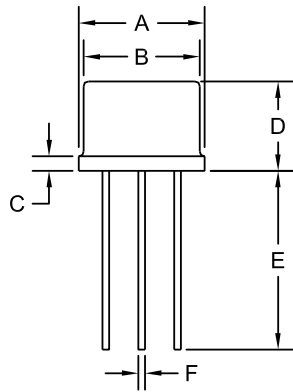
| SYMBOL               | TEST CONDITIONS  | MIN | MAX | UNITS |
|----------------------|--|-----|-----|-------|
| I <sub>CBO</sub>     | V <sub>CB</sub> =60V   |     | 50  | nA    |
| I <sub>CBO</sub>     | V <sub>CB</sub> =60V, (T <sub>C</sub> =150°C)  |     | 50  | μA    |
| I <sub>EBO</sub>     | V <sub>EB</sub> =5.0V  |     | 100 | nA    |
| BV <sub>CBO</sub>    | I <sub>C</sub> =100μA  | 60  |     | V     |
| BV <sub>CER</sub>    | I <sub>C</sub> =100mA, R <sub>BE</sub> =10Ω  | 60  |     | V     |
| BV <sub>CEO</sub>    | I <sub>C</sub> =100mA  | 45  |     | V     |
| BV <sub>EBO</sub>    | I <sub>E</sub> =100μA  | 7.0 |     | V     |
| V <sub>CE(SAT)</sub> | I <sub>C</sub> =150mA, I <sub>B</sub> =15mA  |     | 0.9 | V     |
| V <sub>BE(SAT)</sub> | I <sub>C</sub> =150mA, I <sub>B</sub> =15mA  |     | 1.2 | V     |
| h <sub>FE</sub>      | V <sub>CE</sub> =10V, I <sub>C</sub> =1.0mA  | 30  |     |       |
| h <sub>FE</sub>      | V <sub>CE</sub> =10V, I <sub>C</sub> =150mA  | 50  | 200 |       |
| h <sub>fe</sub>      | V <sub>CE</sub> =10V, I <sub>C</sub> =5.0mA, f=1.0kHz                                  | 50  | 275 |       |
| f <sub>T</sub>       | V <sub>CE</sub> =10V, I <sub>C</sub> =50mA   | 100 |     | MHz   |
| C <sub>ob</sub>      | V <sub>CB</sub> =10V, I <sub>E</sub> =0  |     | 15  | pF    |
| C <sub>ib</sub>      | V <sub>BE</sub> =0.5V, I <sub>C</sub> =0   |     | 80  | pF    |
| NF                   | V <sub>CE</sub> =10V, I <sub>C</sub> =0.3mA, f=1.0kHz, R <sub>G</sub> =1.0kΩ, BW=1.0Hz |     | 10  | dB    |

R0 (17-August 2012)

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**TO-39 CASE - MECHANICAL OUTLINE**



| SYMBOL  | INCHES |       | MILLIMETERS |      |
|---------|--------|-------|-------------|------|
|         | MIN    | MAX   | MIN         | MAX  |
| A (DIA) | 0.335  | 0.370 | 8.51        | 9.40 |
| B (DIA) | 0.315  | 0.335 | 8.00        | 8.51 |
| C       | -      | 0.040 | -           | 1.02 |
| D       | 0.240  | 0.260 | 6.10        | 6.60 |
| E       | 0.500  | -     | 12.70       | -    |
| F (DIA) | 0.016  | 0.021 | 0.41        | 0.53 |
| G (DIA) | 0.200  |       | 5.08        |      |
| H       | 0.100  |       | 2.54        |      |
| I       | 0.028  | 0.034 | 0.71        | 0.86 |
| J       | 0.029  | 0.045 | 0.74        | 1.14 |

TO-39 (REV: R1)

**LEAD CODE:**

- 1) Emitter
- 2) Base
- 3) Collector

**MARKING: FULL PART NUMBER**

R0 (17-August 2012)

## OUTSTANDING SUPPORT AND SUPERIOR SERVICES



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### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

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### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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### REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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### CONTACT US

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